

Amendments to the Specification:

Please amend paragraph [0001] as follows:

[0001] This application claims the priority benefit of Taiwan application serial no. 92120050, filed ~~Jul.~~July 23, 2003. This application is ~~related to a continuation-in-part of application Ser. No. 10/445,558, filed on May 27, 2003, which is a continuation-in-part of U.S. Pat. No. 6,897,507, to Ser. No. 10/303,451, filed on Nov. 25, 2002, which is a continuation of to~~ U.S. Pat. No. 6,489,647, filed on ~~May.~~May 28, 2002, ~~which is a division of to~~ U.S. Pat. No. 6,455,885, filed on Oct. 03, 2001, ~~which is a division of to~~ U.S. Pat. No. 6,303,423, filed on Nov. 27, 2000, ~~which is a continuation-in-part of application to Ser. No. 09/637,926, filed on Aug. 14, 2000, which is a continuation-in-part of to~~ U.S. Pat. No. 6,383,916, filed on Feb. 17, 1999, ~~which is a continuation-in-part of application and to Ser. No. 09/216,791, filed on Dec. 21, 1998.~~

Please amend paragraph [0025] as follows:

[0025] Afterwards, a passivation layer 126 140 is formed over the dielectric layers 122 and 124 and the circuit layers 132 and 134, covering the electrode 152 and the electromagnetic-field shielding layer 160. The passivation layer 126 150 has a thickness t, for example, larger than 0.35 microns. It should be noted that the passivation layer 126 150 should be thick enough to prevent moisture, impurities, mobile ions or transitional metal elements from penetrating therethrough. The passivation layer 126 140 has openings 128 and 129 exposing the electrode 152 and the circuit layer 134. The openings 129 have a width, for example, ranging from 0.1 microns to 20 microns. The passivation layer 126 150 can be a silicon-dioxide layer, a silicon-nitride layer, a phosphosilicate-glass (PSG) layer, a silicon oxynitride layer or a composite structure by depositing some or all of the above-mentioned dielectric layers.